imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



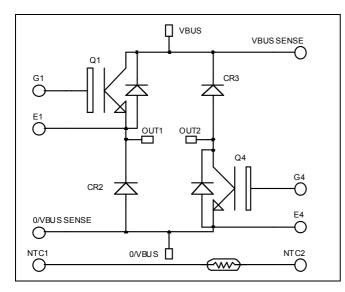
Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





Asymmetrical - Bridge NPT IGBT Power Module



U VBUS \mathbf{O} 0 G4 🕯 OUT2 SENSE E4 🛿 VBUS 0/VBUS OUTI E1 0/VBUS NTC2 \bigcirc SENSE D NTC1 0 Ğı

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	75	
I _C	Continuous Conector Current	$T_c = 80^{\circ}C$	50	А
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	100A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

$V_{CES} = 1200V$ $I_{C} = 50A$ (a) $Tc = 80^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive T_C of V_{CEsat}
- Low profile
- RoHS compliant



All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
т	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	μA
I _{CES}		$V_{CE} = 1200V$	$T_{i} = 125^{\circ}C$			500	μΑ
V	Callester Engitter externation Valtered	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	N/
V _{CE(sat)}	Collector Emitter saturation Voltage	$I_C = 50A$	$T_{j} = 125^{\circ}C$		4.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1 \text{ mA}$		4.5		6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20 V, V_{CE}$	$V_{GE} = 20 \text{ V}, V_{CE} = 0 \text{ V}$			100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			3450		
C _{oes}	Output Capacitance				330		pF
C _{res}	Reverse Transfer Capacitance				220		
Qg	Total gate Charge	$V_{GS} = 15V$			330		
Q _{ge}	Gate – Emitter Charge	$V_{Bus} = 600V$			35		nC
Q _{gc}	Gate – Collector Charge	$I_{\rm C} = 50 {\rm A}$			200		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			35		
Tr	Rise Time	$V_{GE} = 15V$			65		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 50A$ $R_G = 5 \Omega$			320		ns
T _f	Fall Time				30		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$ $R_G = 5 \Omega$			35		
T _r	Rise Time				65		
T _{d(off)}	Turn-off Delay Time				360		ns
T _f	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		6.9		mI
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 50 {\rm A}$ $R_{\rm G} = 5 \ \Omega$	$T_j = 125^{\circ}C$		3.05		mJ

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	μA
I _F	DC Forward Current		$T_j = 125^{\circ}C$ $Tc = 70^{\circ}C$		100	500	A
	Diode Forward Voltage	$I_{\rm F} = 100 {\rm A}$			2.0	2.5	
V _F		$I_{\rm F} = 200 {\rm A}$			2.3		V
		$I_{\rm F} = 100 {\rm A}$	$T_{j} = 125^{\circ}C$		1.8		
t _{rr}	Reverse Recovery Time	$I_{\rm F} = 100 \text{A}$ $V_{\rm R} = 800 \text{V}$	$T_j = 25^{\circ}C$		420		ns
ι _{rr}			$T_{j} = 125^{\circ}C$		580		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 A/\mu s$	$T_j = 25^{\circ}C$		1250		nC
			$T_{j} = 125^{\circ}C$		5350		пс



Thermal and package characteristics

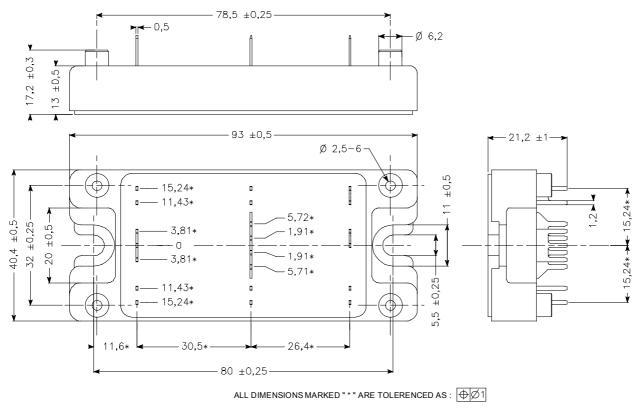
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.4	°C/W
			Diode			0.55	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range		-40		150		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP4 Package outline (dimensions in mm)



See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com



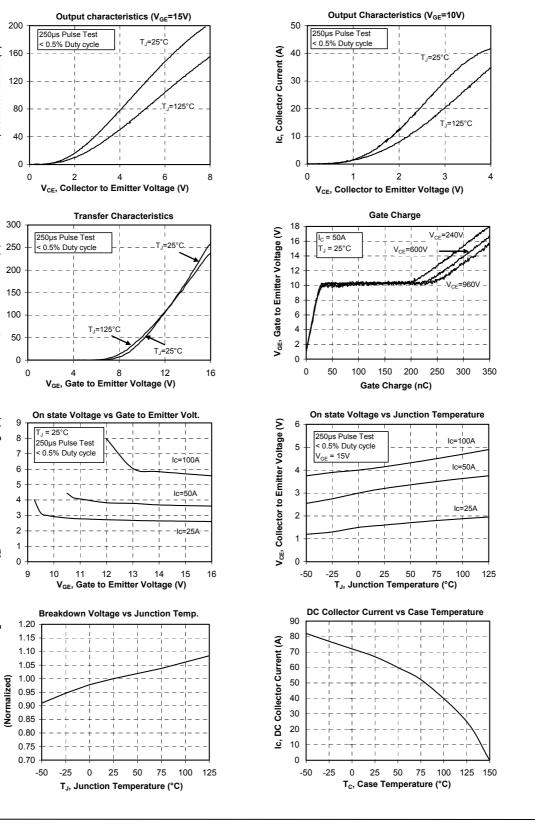
Typical Performance Curve

Ic, Collector Current (A)

Ic, Collector Current (A)

V_{CE}, Collector to Emitter Voltage (V)

Collector to Emitter Breakdown Voltage

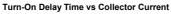


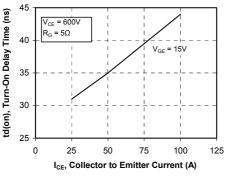
APTGF50DH120TG

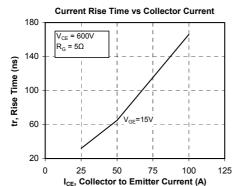
www.microsemi.com

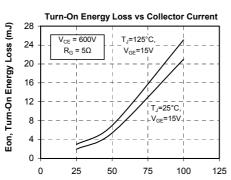
4 - 7



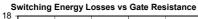


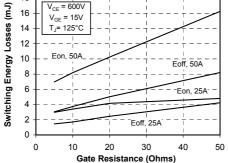




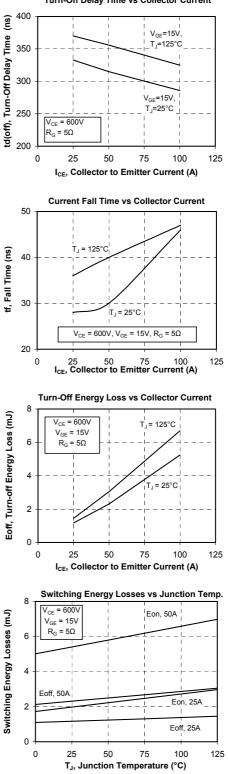






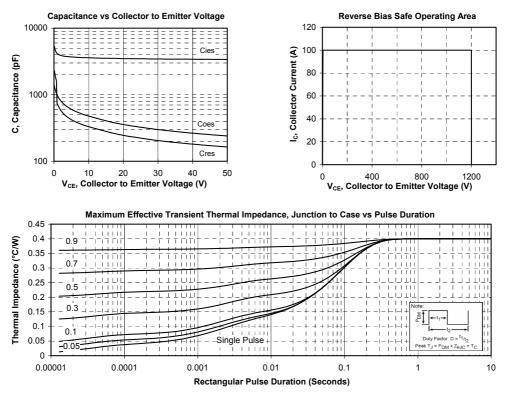


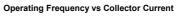
Turn-Off Delay Time vs Collector Current

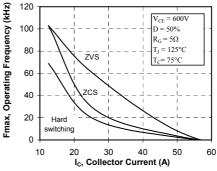


www.microsemi.com











DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with lifesupport or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.